High-Power NPN Silicon Transistor

High–power NPN silicon transistors are for use in power amplifier and switching circuits applications.

Features

- Low Collector–Emitter Saturation Voltage $V_{CE(sat)} = 0.75 \text{ Vdc (Max)} @ I_C = 10 \text{ Adc}$
- Pb-Free Package is Available*

MAXIMUM RATINGS (Note 1) ($T_J = 25^{\circ}C$ unless otherwise noted)

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V _{CEO}	60	Vdc
Collector-Base Voltage	V_{CB}	60	Vdc
Collector Current – Continuous (Note 2)	I _C	30	Adc
Base Current	Ι _Β	7.5	Adc
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	200 1.14	W W/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +200	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$\theta_{\sf JC}$	0.875	°C/W
Thermal Resistance, Case-to-Ambient	$\theta_{\sf CA}$	34	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- 1. Indicates JEDEC Registered Data.
- 2. Pulse Test: Pulse Width = 5 μ s, Duty Cycle \leq 10%.

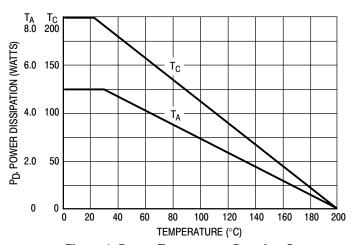


Figure 1. Power Temperature Derating Curve



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30 AMPERES POWER TRANSISTOR NPN SILICON 60 VOLTS, 200 WATTS



TO-204AA (TO-3) CASE 1-07 STYLE 1

MARKING DIAGRAM



2N5302 = Device Code
G = Pb-Free Package
A = Location Code

YY = Year WW = Work Week MEX = Country of Origin

ORDERING INFORMATION

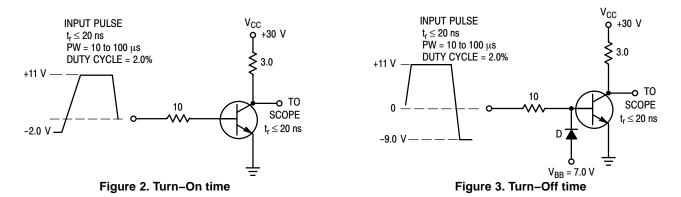
Device	Package	Shipping
2N5302	TO-204	100 Units/Tray
2N5302G	TO-204 (Pb-Free)	100 Units/Tray

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

	Characteristic	ristic Symbol		Mi	n	Ма	ах	Unit
OFF CHARACTERIST	ICS (Note 3)	ı					1	
Collector–Emitter Susta (I _C = 200 mAdc, I _B	aining Voltage (Note 4) = 0)	V _{Cl}	V _{CEO(sus)} 60			_		Vdc
Collector Cutoff Curren (V _{CE} = 60 Vdc, I _B =		I	I _{CEO} -			- 5.0		mAdc
Collector Cutoff Curren (V _{CE} = 60 Vdc, V _{EB}		I	I _{CEX}			1.0		mAdc
Collector Cutoff Curren (V _{CE} = 60 Vdc, V _{EB}	nt _{B(Off)} = 1.5 Vdc, T _C = 150°C)	I _{CEX}			- 10			mAdc
Collector Cutoff Curren (V _{CB} = 80 Vdc, I _E =		I	- 1.0)	mAdc	
Emitter Cutoff Current	(V _{BE} = 5.0 Vdc, I _C = 0)	I	EBO	_		5.)	mAdc
ON CHARACTERISTIC	cs	•			•		•	
DC Current Gain (Note * (I _C = 1.0 Adc, V _{CE} * (I _C = 15 Adc, V _{CE} * (I _C = 30 Adc, V _{CE}	= 2.0 Vdc) = 2.0 Vdc)		h _{FE} 40 15 5.0		5	- 60 -		-
*Collector–Emitter Satu ($I_C = 10$ Adc, $I_B = 1$ ($I_C = 20$ Adc, $I_B = 2$ ($I_C = 30$ Adc, $I_B = 6$.0 Adc)2	V ₍	V _{CE(sat)}		2.0		0	Vdc
*Base Emitter Saturation ($I_C = 10$ Adc, $I_B = 1$ ($I_C = 15$ Adc, $I_B = 1$ ($I_C = 20$ Adc, $I_B = 2$.0 Adc) .5 Adc)	V _{BE(sat)} –			- 1.7 - 1.8 - 2.5		3	Vdc
*Base–Emitter On Voltage (Note 4) $(I_C = 15 \text{ Adc}, V_{CE} = 2.0 \text{ Vdc})$ $(I_C = 30 \text{ Adc}, V_{CE} = 4.0 \text{ Vdc})$						1. ⁻ 3.		Vdc
DYNAMIC CHARACTE	ERISTICS (Note 3)							
Current-Gain - Bandw		f _T	2.0		0 –		MHz	
Small-Signal Current Gain (I _C = 1.0 Adc, V _{CE} = 10 Vdc, f = 1.0 kHz) h _{fe}			40)	_		-	
SWITCHING CHARAC	TERISTICS (Note 3)					_		
Rise Time			t _r		- 1.		1.0	μs
Storage Time	$(V_{CC} = 30 \text{ Vdc}, I_C = 10 \text{ Adc}, I_{B1} = I_{B2} = 1.0 \text{ Adc})$		ts	t _s		- 2.0		μs
Fall Time		t _f		-			1.0	μs

SWITCHING TIME EQUIVALENT TEST CIRCUITS



Indicates JEDEC Registered Data.
 Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

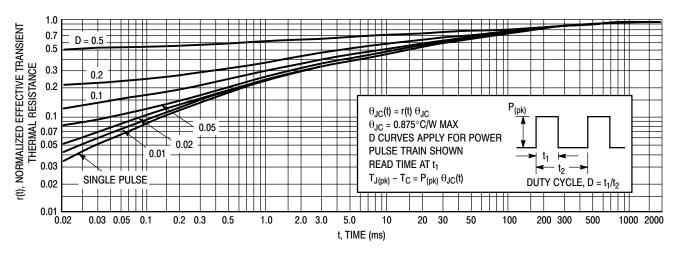


Figure 4. Thermal Response

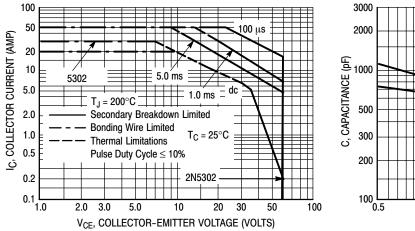


Figure 5. Active-Region Safe Operating Area

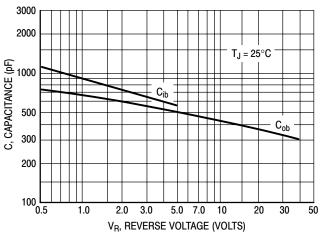


Figure 6. Capacitance versus Voltage

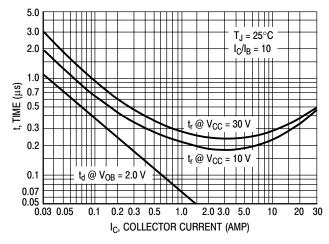


Figure 7. Turn-On Time

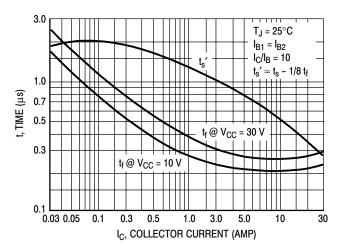


Figure 8. Turn-Off Time

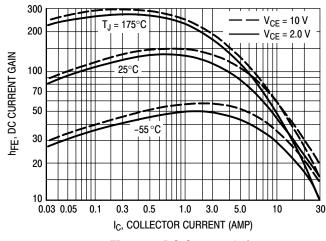


Figure 9. DC Current Gain

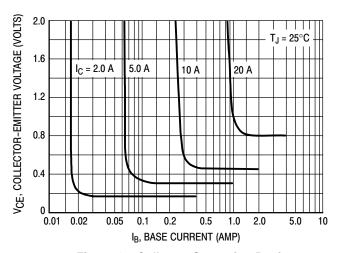


Figure 10. Collector Saturation Region

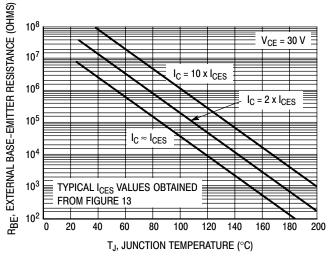


Figure 11. Effects of Base-Emitter Resistance

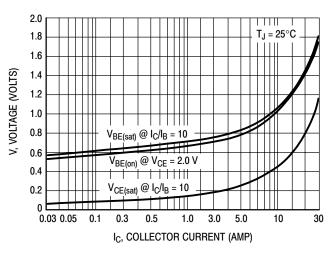


Figure 12. "On" Voltages

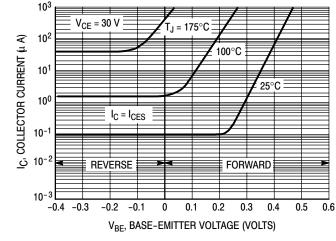


Figure 13. Collector Cut-Off Region

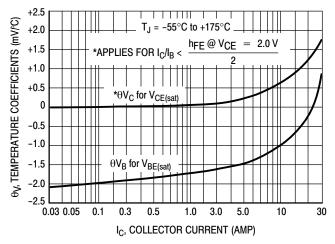
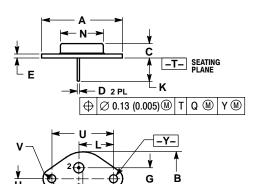


Figure 14. Temperature Coefficients

2N5302

PACKAGE DIMENSIONS

TO-204 (TO-3) **CASE 1-07** ISSUE Z



⊕ Ø 0.13 (0.005) M T Y M

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- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.
- 3. ALL RULES AND NOTES ASSOCIATED WITH REFERENCED TO-204AA OUTLINE SHALL APPLY.

	INC	HES	MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	1.550	1.550 REF		'REF	
В		1.050		26.67	
С	0.250	0.335	6.35	8.51	
D	0.038	0.043	0.97	1.09	
Е	0.055	0.070	1.40	1.77	
G	0.430 BSC		10.92 BSC		
Н	0.215	BSC	5.46 BSC		
K	0.440	0.480	11.18	12.19	
L	0.665 BSC		16.89 BSC		
N		0.830		21.08	
Q	0.151	0.165	3.84	4.19	
U	1.187	BSC	30.15 BSC		
V	0 131	0 188	3 33	4 77	

PIN 1. BASE 2. EMITTER CASE: COLLECTOR

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